



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

42A

Features

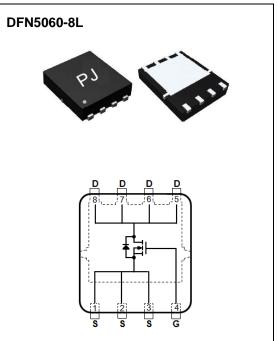
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A<25m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@15A<28.5m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		
Continuous Drain Current (Note 4)	T _C =25°C	I _D	42	А	
	T _C =100°C		26.6		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	150		
Power Dissipation	T _C =25°C	Po	83	101	
	T _C =100°C		33	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	6.5		
	T _A =70°C		5.2	Α	
Power Dissipation	T _A =25°C	Po	2	101	
	T _A =70°C		1.3	W	
Single Pulse Avalanche Energy (Note 6)		E _{AS}	63.4	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	1.5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA V _{DS} =V _{GS} , I _D =250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$		1	1.8	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =20A	-	20	25	mΩ
		V _{GS} =4.5V,I _D =15A	-	22	28.5	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =80V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	V _{DS} =50V, I _D =10A, V _{GS} =10V ^(Note 1,2)	-	31	-	nC
Gate-Source Charge	Q_gs		-	5.1	-	
Gate-Drain Charge	Q_{gd}		-	7.3	-	
Input Capacitance	Ciss	V_{DS} =30V, V_{GS} =0V, f =1MHZ	-	1519	-	pF
Output Capacitance	Coss		-	132	-	
Reverse Transfer Capacitance	Crss		-	66	-	
Turn-On Delay Time	td _(on)	V 50V I 40A	-	11	-	ns
Turn-On Rise Time	t _r	V_{DD} =50V, I_{D} =10A, V_{GS} =10V, R_{G} =3 Ω (Note 1,2)	-	42	-	
Turn-Off Delay Time	td _(off)		-	40	-	
Turn-Off Fall Time	t _f		-	19	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	ı				42	Α
Diode Forward Current	I _S		-	-	42	A
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.7	1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. RΘ_{JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=3mH, I_{AS} =6.5A, V_{DD} =50V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

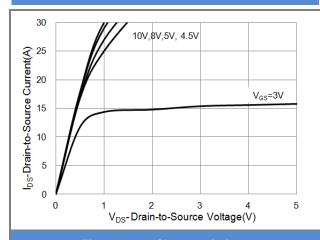


Fig.1 Output Characteristics

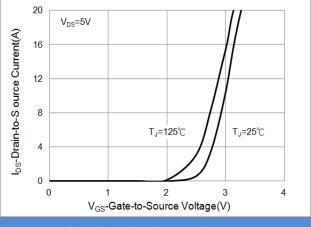


Fig.2 Transfer Characteristics

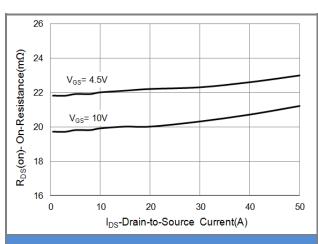


Fig.3 On-Resistance vs. Drain Current

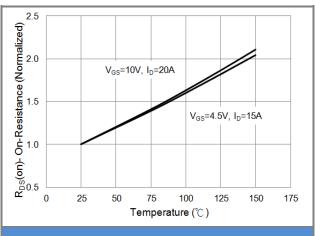
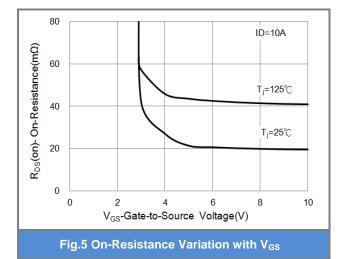


Fig.4 On-Resistance vs. Junction temperature



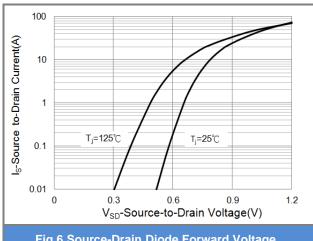


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

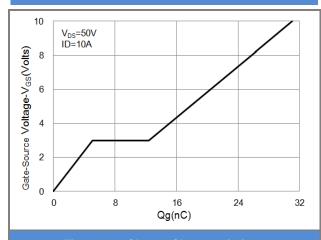


Fig.7 Gate-Charge Characteristics

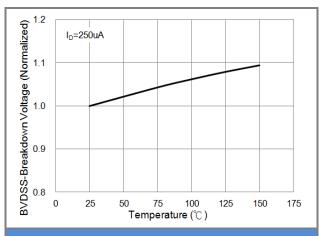


Fig.8 Breakdown Voltage Variation vs. Temperature

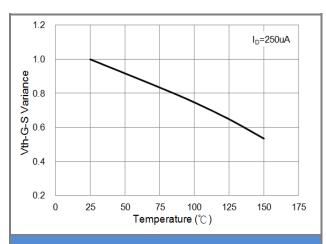


Fig.9 Threshold Voltage Variation with Temperature

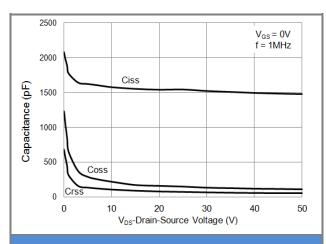


Fig.10 Capacitance vs. Drain-Source Voltage

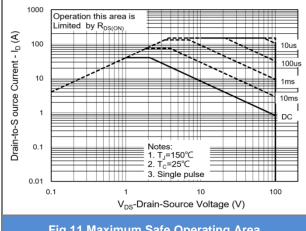


Fig.11 Maximum Safe Operating Area

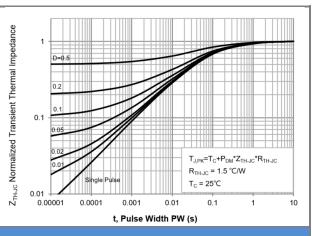


Fig.12 Normalized Transient Thermal Impedance

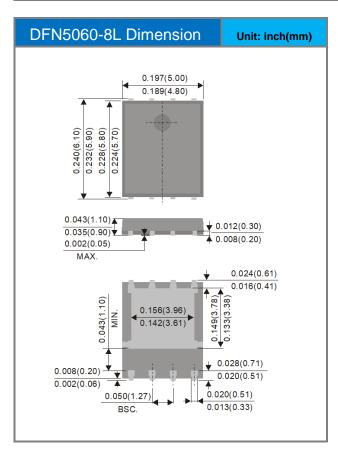


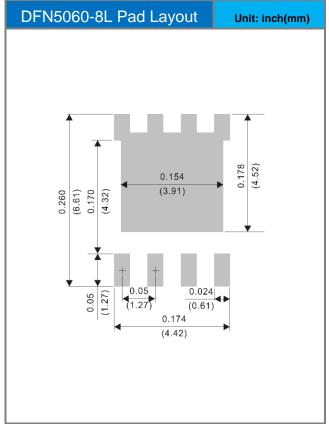


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5476AL-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5476AL	Halogen free	

Packaging Information & Mounting Pad Layout









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